

NTE14 Silicon PNP Transistor High Power, Low Frequency Driver

Features:

- High Power Compact FTR Package: $P_C = 750\text{mW}$
- High Breakdown Voltage: $V_{CEO} = 80\text{V}$

Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Collector–Base Voltage, V_{CBO}	80V
Collector–Emitter Voltage, V_{CEO}	80V
Emitter–Base Voltage, V_{EBO}	5V
Collector Current, I_C	700mA
Collector Dissipation, P_C	750mW
Junction Temperature, T_J	+135°C
Storage Temperature Range, T_{stg}	–55° to +135°C

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector–Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 2\text{mA}$	80	–	–	V
Collector–Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 50\mu\text{A}$	80	–	–	V
Emitter–Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 50\mu\text{A}$	5	–	–	V
Collector Cutoff Current	I_{CBO}	$V_{CB} = 50\text{V}$	–	–	0.5	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 4\text{V}$	–	–	0.5	μA
DC Current Gain	h_{FE}	$V_{CE} = 3\text{V}, I_C = 100\text{mA}$	120	–	270	–
Collector Saturation Voltage	$V_{CE(sat)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$	–	0.2	0.4	V
Transition Frequency	f_T	$V_{CE} = 10\text{V}, I_E = 50\text{mA}$	–	100	–	MHz
Output Capacitance	C_{ob}	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$	–	14	20	pF

